
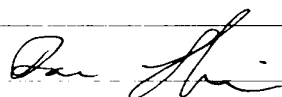


Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5649-805DV		Serial No. To Be Assigned	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Kang-Wook Park		GAU:	
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